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PRG2001-5CD3

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: *King*) Art Unit: 2811
Serial No.: 10/828,356)
Filed: 4/19/2004 as a divisional of) Examiner: Unknown
10/298,916 now U.S. patent 6,724,024)
For: *Charge trapping pull up element*)

INFORMATION DISCLOSURE STATEMENT

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

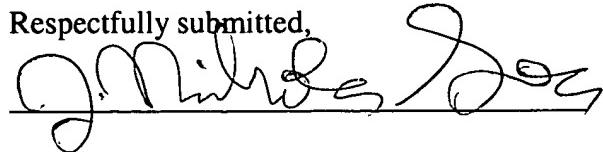
Sir:

1. Pursuant to 37 C.F.R. 1.97 and 1.98, and in compliance with 37 C.F.R. 1.56, the Office's attention is directed to the patents, publications and other information listed on the attached PTO-1449. Regarding the document(s), publication(s) or other information listed on the attached PTO-1449, Applicant believes the same may qualify as "prior" art to this application and should be treated accordingly, although Applicant(s) reserve(s) the right to contest the prior art status of any document, publication or information cited herein.

2. Pursuant to 37 C.F.R. 1.97(b) this Statement is being filed before the mailing date of a first Office action on the merits.

3. Copies of the aforementioned references were provided by the applicant and/or cited by the respective examiner in the related parent applications to the above. Should it be necessary for the applicant to provide additional copies of any other references, please contact the undersigned.

Respectfully submitted,



July 22, 2004
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I hereby certify that the foregoing is being deposited with the U.S. Postal Service, postage prepaid, to Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, this 22nd day of July 2004



Information Disclosure Statement By Applicant

Substitute for form 1449/PTO

Page 1 of 7

Application Number: 10/828,356

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First Named Inventor: King

Art Unit: 2811

Examiner Name: N/A

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Information Disclosure Statement By Applicant

Substitute for form 1449/PTO

Page 2 of 7

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Substitute for form 1449/PTO

Page 3 of 7

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Substitute for form 1449/PTO

Page 4 of 7

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Page 5 of 7

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Page 6 of 7

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Page 7 of 7

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